

In the Specification:

Please amend the paragraph on Page 4, lines 28-31 as follows:

Further, FIG. 3 is a graph illustrating breakdown voltage characteristics of a high voltage device $\text{C} \underline{\text{D}}$ in which the gate electrode is formed using the polysilicon film formed while applying evaporation, and a high voltage device $\text{D} \underline{\text{C}}$ in which a gate electrode is formed using a polysilicon film that is formed without applying vacuum.